捷多邦,专业PCB打样工厂,24小时**SNIJ4G**TLPH16912 18-BIT LVTTL-TO-GTL+ UNIVERSAL BUS TRANSCEIVER

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- UBT™ (Universal Bus Transceiver)
 Combines D-Type Latches and D-Type
 Flip-Flops for Operation in Transparent,
 Latched, Clocked, and Clock-Enabled Mode
- Bidirectional Interface Between GTL+ Signal Levels and LVTTL Logic Levels
- LVTTL Interfaces Are 5-V Tolerant
- Identical to '16601 Function
- Medium-Drive GTL+ Outputs (50 mA)
- LVTTL Outputs (-24 mA/24 mA)
- GTL+ Rise and Fall Times Designed for Optimal Data-Transfer Rate and Signal Integrity
- I_{off}, Power-Up 3-State, and BIAS V_{CC} Support Live Insertion
- Bus Hold on A-Port Data Inputs
- Distributed V_{CC} and GND-Pin Configuration Minimizes High-Speed Switching Noise
- Package Options Include Plastic Thin Shrink Small-Outline (DGG), Thin Very Small-Outline (DGV), and Shrink Small-Outline (DL) Packages

NOTE: For tape and reel order entry:
The DGGR package is abbreviated to GR, and the DGVR package is abbreviated to VR.

description

The SN74GTLPH16912 is a medium-drive 18-bit universal bus transceiver (UBT) that provides LVTTL-to-GTL+ and GTL+-to-LVTTL signal-level translation. It allows for transparent, latched,

clocked, and clock-enabled modes of data transfer identical to the '16601 function. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTL+ signal levels. High-speed (about two times faster than standard TTL or LVTTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, and output edge control (OEC™). Improved GTLP OEC circuits minimize bus settling time and have been designed and tested using several backplane models. The medium drive is suitable for driving double-terminated backplanes.

GTL+ is the Texas Instruments derivative of the Gunning transceiver logic (GTL) JEDEC standard JESD 8-3. The AC specification of the SN74GTLPH16912 is given only at the preferred higher noise margin GTL+, but the user has the flexibility of using this device at either GTL ($V_{TT} = 1.2 \text{ V}$ and $V_{REF} = 0.8 \text{ V}$) or GTL+ ($V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$) signal levels.

Normally, the B port operates at GTL or GTL+ levels, while the A-port and control inputs are compatible with LVTTL logic levels and are 5-V tolerant. V_{REF} is the reference input voltage for the B port.



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description (continued)

This device is fully specified for live-insertion applications using $I_{\rm off}$, power-up 3-state, and BIAS $V_{\rm CC}$. The $I_{\rm off}$ circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS $V_{\rm CC}$ circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

Active bus-hold circuitry holds unused or undriven LVTTL inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable (\overline{OE}) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74GTLPH16912 is characterized for operation from -40°C to 85°C.

functional description

The SN74GTLPH16912 is a medium-drive (50 mA) 18-bit UBT containing D-type latches and D-type flip-flops for data-path operation in transparent, latched, clocked, or clock-enabled modes and can replace any of the functions shown in Table 1.

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT	18 BIT
Transceiver	'245, '623, '645	'863	'861	'16245, '16623	'16863
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541	'16825
Latched transceiver	'543			'16543	'16472
Latch	'373, '573	'843	'841	'16373	'16843
Registered transceiver	'646, '652			'16646, '16652	'16474
Flip-flop	'374, '574		'821	'16374	
Standard UBT					'16500, '16501
Universal bus driver					'16835
Registered transceiver with CLK enable	'2952			'16470, '16952	
Flip-flop with CLK enable	'377	'823			'16823
Standard UBT with CLK enable					'16600, '16601
SN74G	TLPH16912 UBT re	eplaces all	above fur	nctions	_

Table 1. SN74GTLPH16912 UBT Replacement Functions

Data flow in each direction is controlled by output-enable (\overline{OEAB} and \overline{OEBA}), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. The clock can be controlled by clock-enable (\overline{CEAB} and \overline{CEBA}) inputs. \overline{OEAB} and \overline{OEBA} control the 18 bits of data for the A-to-B and B-to-A directions, respectively.

For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CEAB is low and CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB if CEAB also is low. When OEAB is low, the outputs are active. When OEAB is high, the outputs are in the high-impedance state.

Data flow for B to A is similar to that for A to B, but uses OEBA, LEBA, CLKBA, and CEBA.

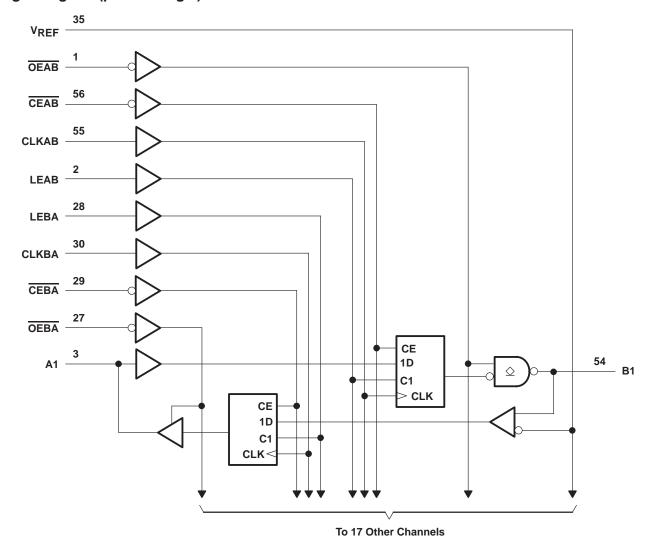


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	INPUTS			ОИТРИТ	MODE	
CEAB	OEAB	LEAB	CLKAB	Α	В	MODE
Х	Н	Х	Х	Χ	Z	Isolation
L	L	L	Н	Χ	В ₀ ‡ В ₀ §	Latabad storage of A data
L	L	L	L	Χ	В ₀ §	Latched storage of A data
Х	L	Н	Х	L	L	Transparent
Х	L	Н	Χ	Н	Н	Transparent
L	L	L	\uparrow	L	L	Clasked storage of A data
L	L	L	\uparrow	Н	Н	Clocked storage of A data
Н	L	L	Х	Χ	В ₀ §	Clock inhibit

[†]A-to-B data flow is shown. B-to-A data flow is similar but uses OEBA, LEBA, CLKBA, and CEBA.

logic diagram (positive logic)



TEXAS

[‡] Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

[§] Output level before the indicated steady-state input conditions were established

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} and BIAS V_{CC}	–0.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V _O	
(see Note 1): A port	
B port	–0.5 V to 4.6 V
Current into any output in the low state, I _O : A port	48 mA
B port	
Current into any A-port output in the high state, I _O (see Note 2)	48 mA
Continuous current through each V _{CC} or GND	±100 mA
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Package thermal impedance, θ _{JA} (see Note 3): DGG package	
DGV package	
DL package	
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Notes 4 through 6)

			MIN	NOM	MAX	UNIT
V _{CC} , BIAS V _{CC}	Supply voltage		3.15	3.3	3.45	V
\/	Tormination valtage	GTL	1.14	1.2	1.26	V
VTT	Termination voltage	GTL+	1.35	1.5	1.65	1 °
\/	Output to college	GTL	0.74	0.8	0.87	V
VREF	Supply voltage	GTL+	0.87	1	1.1]
VI	Input voltogo	B port			VTT	V
	Input voltage	Except B port			Vcc	1 °
V	High-level input voltage	B port	V _{REF} +0.05			V
VIH		Except B port	2			1 °
V	Low level input voltage	B port			V _{REF} -0.05	V
VIL	Low-level input voltage	Except B port	0.8		0.8	1 °
lik	Input clamp current	<u>.</u>			-18	mA
loh	High-level output current	A port			-24	mA
lOL	Law law aloute when the command	A port			24	^
	Low-level output current	B port			50	mA
TA	Operating free-air temperature	-	-40		85	°C

NOTES: 4. All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

- 5. Normal connection sequence is GND first, BIAS $V_{CC} = 3.3 \text{ V}$ second, and $V_{CC} = 3.3 \text{ V}$, I/O, control inputs, V_{TT} and V_{REF} (any order) last. However, if the B-port I/O precharge is not required, the acceptable connection sequence is GND first and $V_{CC} = 3.3 \text{ V}$, BIAS $V_{CC} = 3.3 \text{ V}$, I/O, control inputs, V_{TT} and V_{REF} (any order) last. When V_{CC} is connected, the BIAS V_{CC} circuitry is disabled.
- V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances as long as they do not exceed the DC absolute I_{OL} ratings.
 Similarly, V_{RFF} can be adjusted to optimize noise margins, but normally is 2/3 V_{TT}.



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electrical characteristics over recommended operating free-air temperature range for GTL+ (unless otherwise noted)

P/	ARAMETER	TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT
VIK		V _{CC} = 3.15 V,	I _I = -18 mA			-1.2	V
		V _{CC} = 3.15 V to 3.45 V,	I _{OH} = -100 μA	V _{CC} -0.2			
VOH	A port	V 2.15 V	I _{OH} = -12 mA	2.4			V
		V _{CC} = 3.15 V	$I_{OH} = -24 \text{ mA}$	2			
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	I _{OL} = 100 μA			0.2	
	A port	V _{CC} = 3.15 V	I _{OL} = 12 mA			0.4	
		VCC = 3.13 V	I _{OL} = 24 mA			0.5	
VOL		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	I _{OL} = 100 μA			0.2	V
	B port		$I_{OL} = 10 \text{ mA}$			0.2	
	D port	V _{CC} = 3.15 V	$I_{OL} = 40 \text{ mA}$			0.4	
			$I_{OL} = 50 \text{ mA}$			0.55	
	B port	$V_{CC} = 3.45 \text{ V},$	$V_{I} = 0 \text{ to } 1.5 \text{ V}$			±10	
Ι _Ι ‡	A-port and	Voc = 3.45 V	VI = 0 or VCC			±10	μΑ
	control inputs	V _{CC} = 3.45 V	V _I = 5.5 V			±20	
I _{BHL} §	A port	$V_{CC} = 3.15 \text{ V},$	V _I = 0.8 V	75			μΑ
I _{BHH} ¶	A port	$V_{CC} = 3.15 \text{ V},$	V _I = 2 V	-75			μΑ
I _{BHLO} #	A port	$V_{CC} = 3.45 \text{ V},$	$V_I = 0$ to V_{CC}			500	μΑ
I _{BHHO}	A port	V _{CC} = 3.45 V,	$V_I = 0$ to V_{CC}			-500	μΑ
		V _{CC} = 3.45 V, I _O = 0,	Outputs high			50	
ICC	A or B port	V _I (A-port or control input) = V _{CC} or GND	Outputs low			50	mA
		V_I (B port) = V_{TT} or GND	Outputs disabled			50	
ΔlCC≉		V_{CC} = 3.45 V, One A-port or control input at Other A-port or control inputs at V_{CC} or GNI				1	mA
Ci	Control inputs	V _I = 3.15 V or 0					pF
Cı	A port	V _O = 3.15 V or 0					n.E
C _{io}	B port	V _O = 1.5 V or 0					pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

live-insertion specifications for A port over recommended operating free-air temperature range

PARAMETER		MIN MAX	UNIT		
l _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_I or $V_O = 0$ to 5.5 V	100	μА
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 V \text{ to } 3 V,$	OE = 0	±100	μΑ
I _{OZPD}	$V_{CC} = 1.5 \text{ V to 0},$	$V_0 = 0.5 \text{ V to 3 V},$	OE = 0	±100	μΑ



[‡] For I/O ports, the parameter I_I includes the off-state output leakage current.

[§] The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL}max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL}max.

The bus-hold circuit can source at least the minimum high sustaining current at V_{IH}min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH}min.

[#] An external driver must source at least I_{BHLO} to switch this node from low to high.

An external driver must sink at least I_{BHHO} to switch this node from high to low.

[★]This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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live-insertion specifications for B port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS		MIN	MAX	UNIT
l _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_I or $V_O = 0$ to 1.5 V		100	μΑ
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 \text{ V to } 1.5 \text{ V},$	OE = 0		±100	μΑ
IOZPD	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 \text{ V to } 1.5 \text{ V},$	OE = 0		±100	μΑ
log (PIAS Vog)	V _{CC} = 0 to 3.15 V	PIAS Vac - 2 15 V to 2 45 V	\/_ (D nort)		5	mA
ICC (BIAS VCC)	V _{CC} = 3.15 V to 3.45 V	BIAS V _{CC} = 3.15 V to 3.45 V,	V_O (B port) = 0 to 1.5 V		10	μΑ
Vo	$V_{CC} = 0$,	BIAS V _{CC} = 3.3 V		0.95	1.05	V
IO	$V_{CC} = 0$,	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	V_O (B port) = 0.6 V	-1		μΑ

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTL+ (unless otherwise noted)

			MIN	MAX	UNIT	
fclock	Clock frequency				MHz	
	w Pulse duration	LEAB or LEBA high			20	
t _W	Pulse duration	CLKAB or CLKBA high or low			ns	
		A before CLKAB↑				
		B before CLKBA↑				
	Catura tima	A before LEAB↓				
t _{su}	Setup time B before LEBA↓	B before LEBA↓			ns	
		CEAB before CLKAB↑				
		CEBA before CLKBA↑				
		A after CLKAB↑				
		B after CLKBA↑				
	Halden	A after LEAB↓				
th	Hold time	B after LEBA↓			ns	
		CEAB after CLKAB↑				
		CEBA after CLKBA↑				



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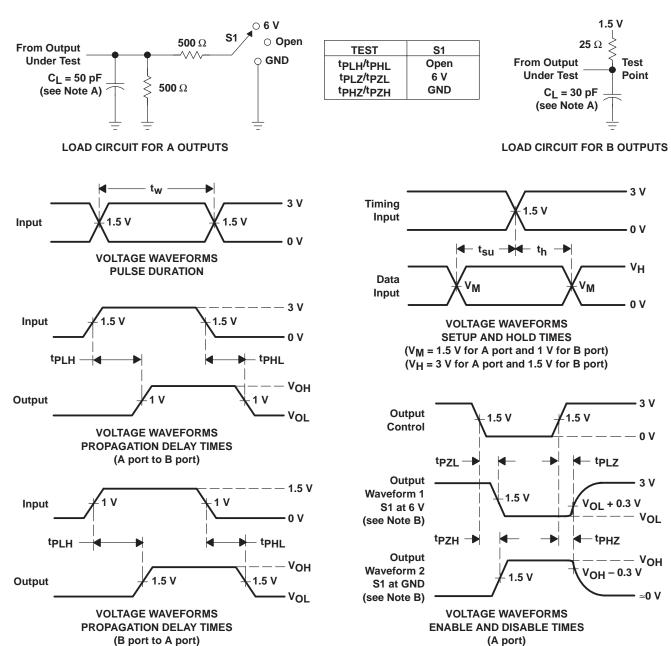
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTL+ (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN TYPT	MAX	UNIT
f _{max}					MHz
	А				
t _{pd}	LEAB	В			ns
	CLKAB				
t _{en}	OFAR	В			no
^t dis	OEAB	Ь			ns
t _r	Rise time, (0.6 V to				ns
tf	Fall time, (1.3 V to	B outputs o 0.6 V)			ns
	В				
t _{pd}	LEBA	А			ns
·	CLKBA	1			
t _{en}	 OEBA	Δ.			no
^t dis	OEDA .	А			ns

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



PARAMETER MEASUREMENT INFORMATION



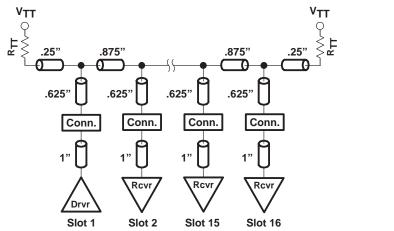
- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
 - D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

This data sheet is specified for and tested to the lump load shown in Figure 1. However, the designer probably uses this GTLP device in a distributed load like that shown in Figure 2, in which actual B-port backplane switching characteristics are different. Therefore, the device is modeled as shown in Figure 3, which very closely matches the results obtained using Figure 2. Switching characteristics based on Figure 3 more closely match actual backplane design requirements.



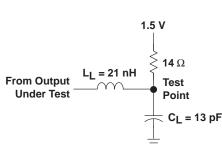


Figure 2. Test Backplane Model

Figure 3. Distributed-Load Circuit for B Outputs

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$ for GTL+ (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN TYP	т мах	UNIT
f _{max}					MHz
	А		I		
^t pd	LEAB	В			ns
•	CLKAB	1			1
t _{en}	 OEAB	В			
^t dis	OEAB	Ь			ns
t _r		Rise time, B outputs (0.6 V to 1.3 V)			ns
t _f		B outputs to 0.6 V)			ns

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



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